

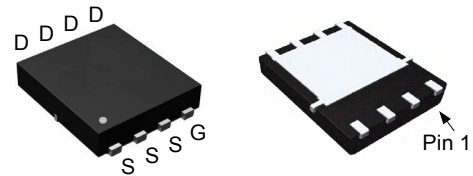
Features

- 30V/-30A
 $R_{DS(ON)} = 9m\Omega (typ.) @ V_{GS} = -10V$
 $R_{DS(ON)} = 13m\Omega (typ.) @ V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- Moisture Sensitivity Level MSL1
(per JEDEC J-STD-020D)

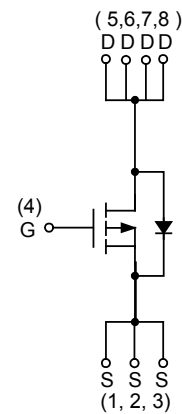
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Pin Description



PDFN5x6-8L



P-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-30	A
I _D	Continuous Drain Current	T _C =25°C	-30	A
		T _C =100°C	-23	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-210	
P _D	Maximum Power Dissipation	T _C =25°C	35.7	W
		T _C =100°C	14.3	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	3.5	°C/W
R _{θJA} ^b	Thermal Resistance-Junction to Ambient	Steady State	55	°C/W
I _{AS} ^c	Avalanche Current, Single pulse	L=0.1mH	-23	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.1mH	26.5	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : Surface Mounted on 1in² pad area.

Note c : UIS tested and pulse width limited by maximum junction temperature (initial temperature T_J=25°C).

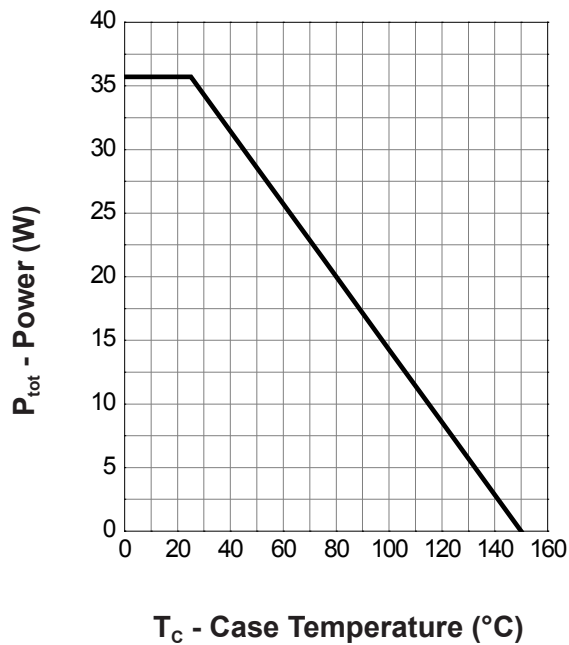
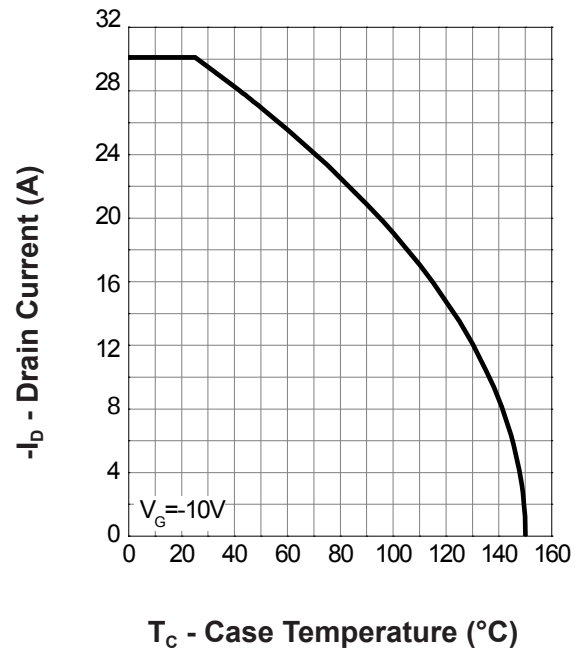
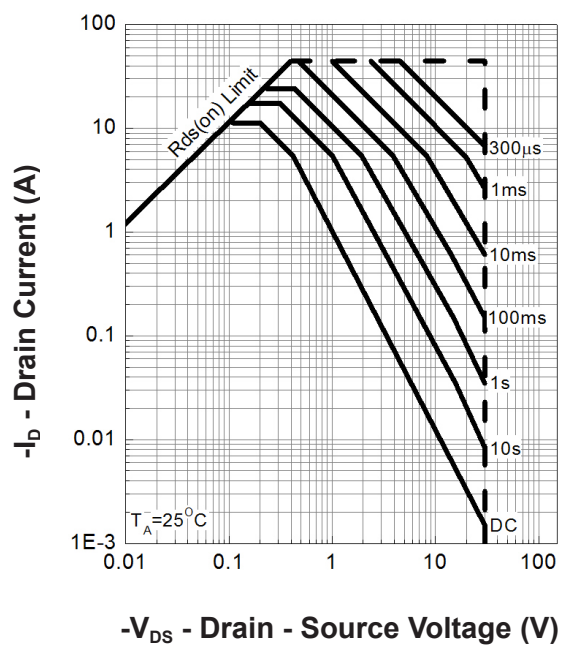
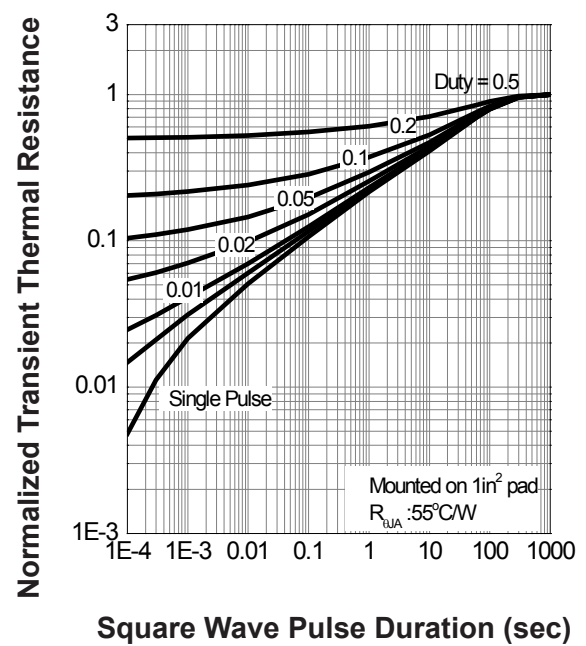
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =85°C	-	-	-1	μA
			-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.2	-1.8	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	μA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-20A V _{GS} =-4.5V, I _{DS} =-12A	-	9 13	12 16	mΩ
			-			
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-20A, V _{GS} =0V	-	-0.85	-1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =-20A, dI _{SD} /dt=100A/μs	-	16	-	ns
Q _{rr}	Reverse Recovery Charge		-	6.3	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	8	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz	-	2110	2990	pF
C _{oss}	Output Capacitance		-	305	-	
C _{rss}	Reverse Transfer Capacitance		-	230	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =15Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	11	20	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	119	214	
t _f	Turn-off Fall Time		-	59	106	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _{DS} =-20A	-	17	-	nC
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _{DS} =-20A	-	33.5	47	
Q _{gs}	Gate-Source Charge		-	5.4	-	
Q _{gd}	Gate-Drain Charge		-	9.2	-	

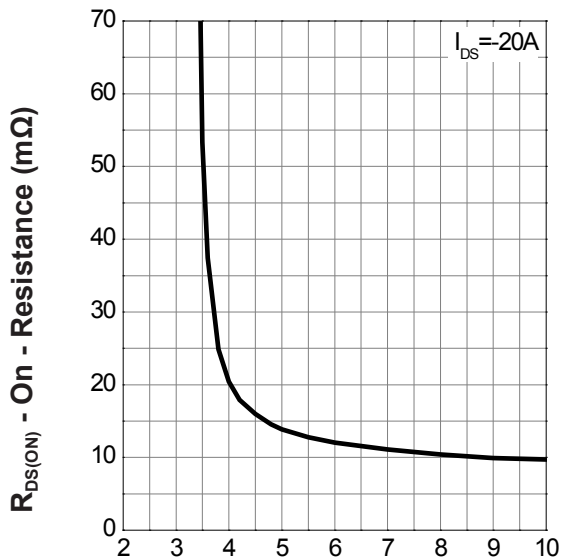
Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

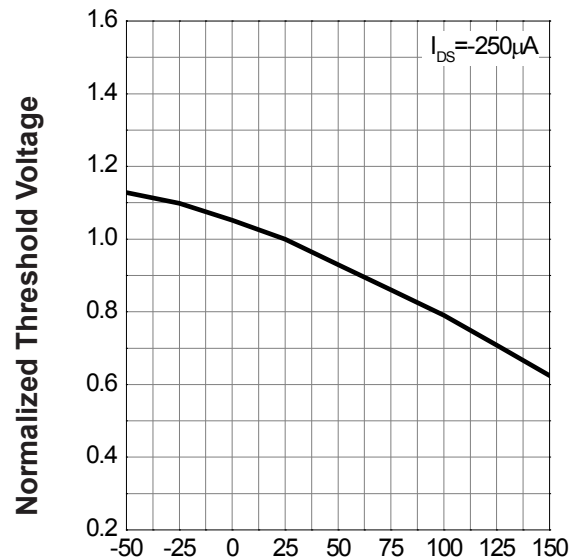
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


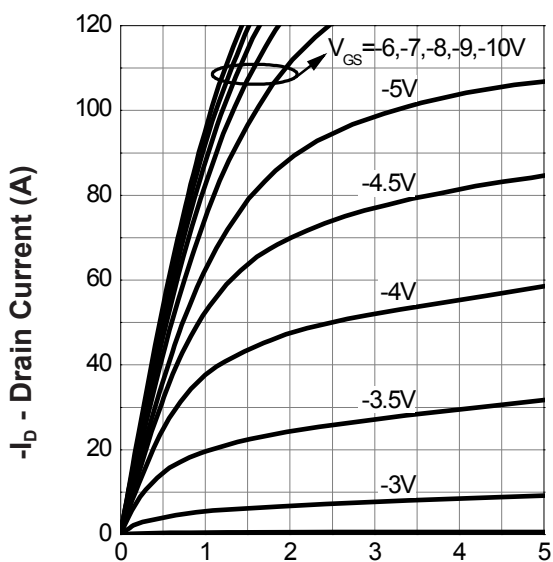
Typical Operating Characteristics(Cont.)

Gate-Source On Resistance


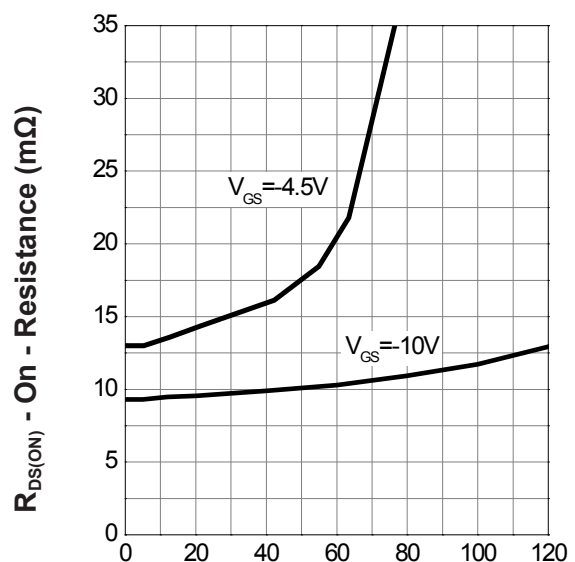
$-V_{GS}$ - Gate - Source Voltage (V)

Gate Threshold Voltage


T_j - Junction Temperature ($^{\circ}C$)

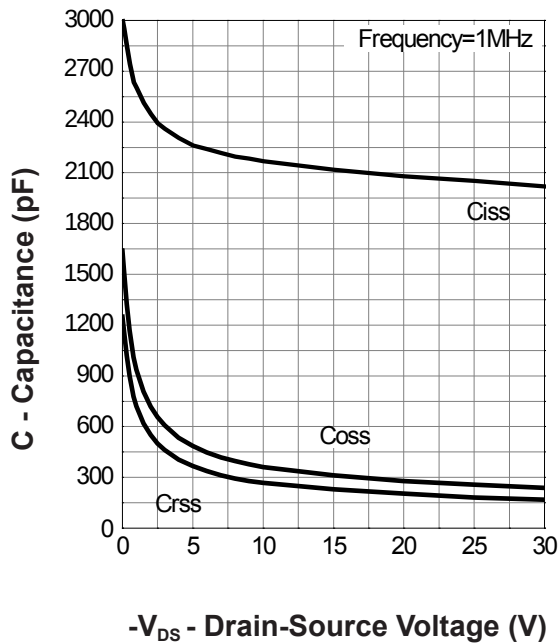
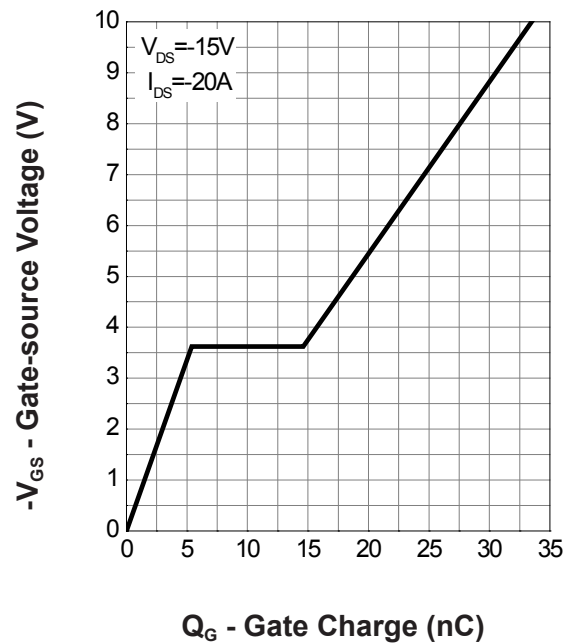
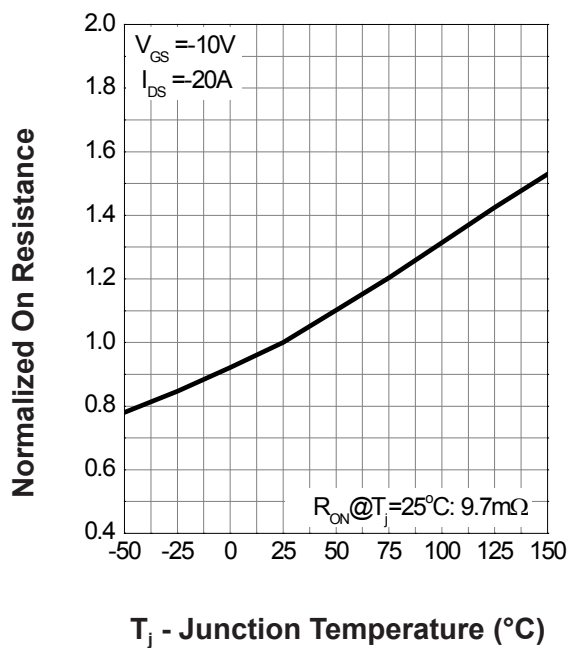
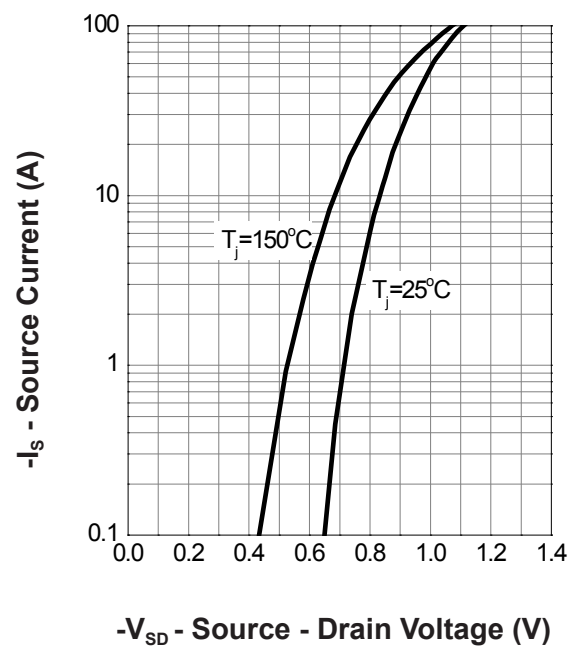
Output Characteristics


$-V_{DS}$ - Drain - Source Voltage (V)

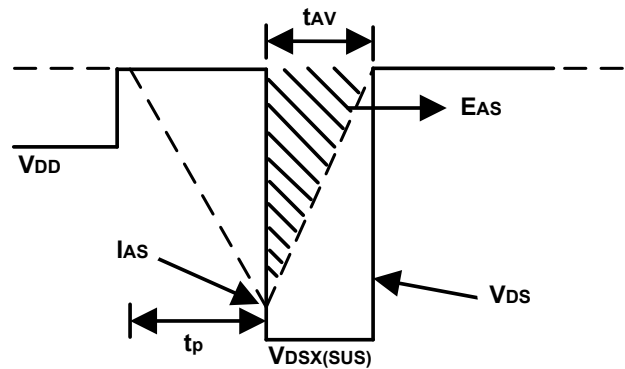
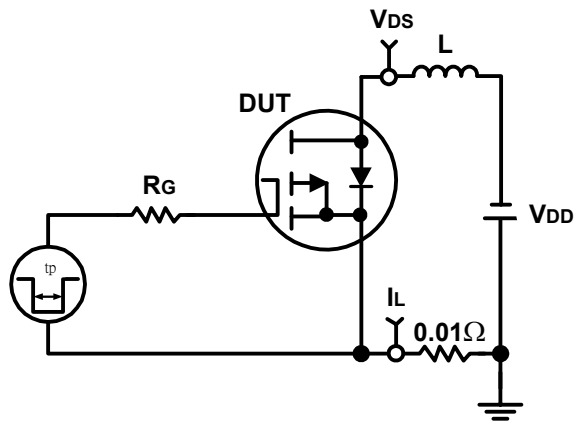
Drain-Source On Resistance


$-I_D$ - Drain Current (A)

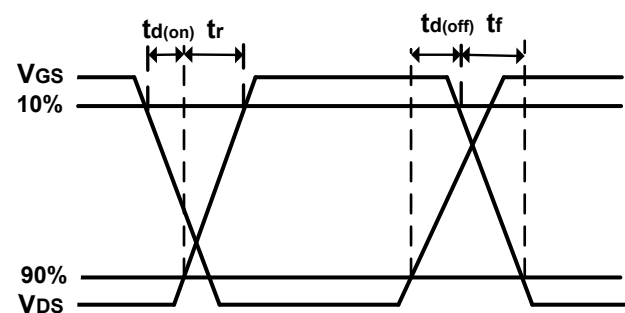
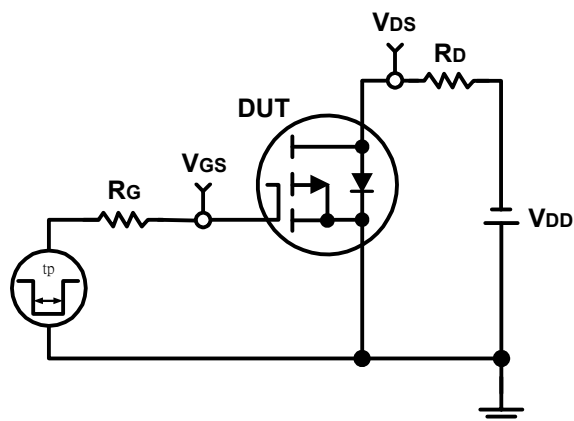
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

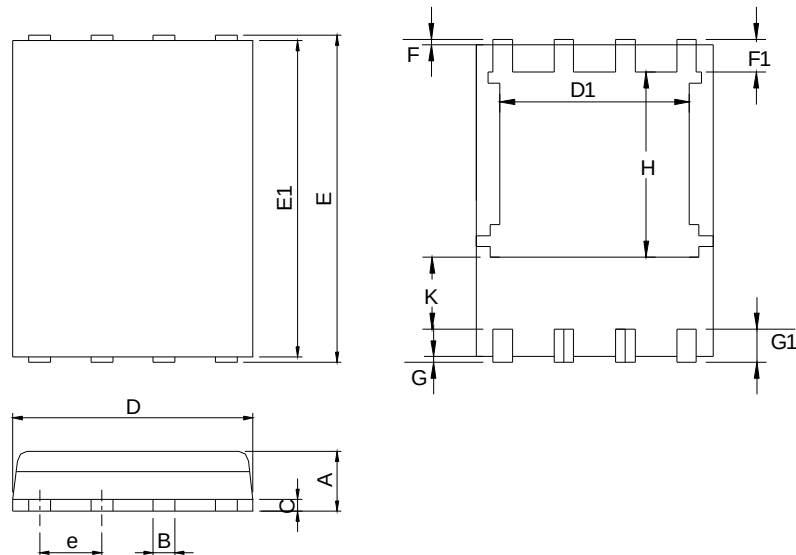


Switching Time Test Circuit and Waveforms



Package Information

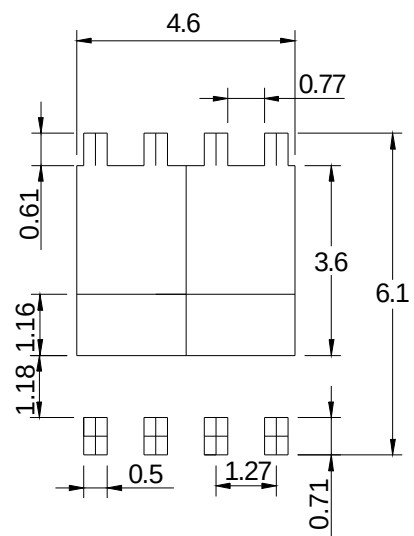
PDFN5x6-8L



SYMBOL	PDFN5x6-8L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN



UNIT: mm